

AMENDMENTS TO THE ABSTRACT

Please substitute the following paragraph(s) for the abstract now appearing in the currently filed specification:

A substrate treatment apparatus, comprising apparatus includes a reaction tube (203) and a heater (207) heating a silicon wafer (200), wherein trimethyl aluminum (TMA) and ozone (O₃) are alternately fed into the reaction tube (203) to generate Al₂O₃ film on the surface of the wafer (200). The apparatus also comprises includes supply tubes (232a) and (232b) for flowing the ozone and TMA and a nozzle (233) supplying gas into the reaction tube (203). The two supply tubes (232a) and (232b) are connected to the nozzle (233) disposed inside the heater (207) in a zone inside the reaction tube (203) where a temperature is lower than a temperature near the wafer (200) wafer, and the ozone and TMA are supplied into the reaction tube (203) through the nozzle (233).